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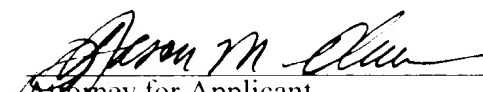
[‡] The Examiner will note that the description regarding Figs. 2B and 2C is also applicable to Figs. 3B, 3C, 4B, 4C, 5B, 5C, 6B and 6C, because these figures show embodiments, which differ from the embodiment shown in Figs. 2B and 2C only in the shape of the compensation patterns.

According to the present invention, as described in the specification, a silicon wafer is over-etched using compensation patterns as a mask (e.g., page 15, line 23 - page 16, line 2). In particular, the silicon wafer is over-etched in a specific manner guided by the shape of the compensation patterns. The compensation patterns, however, are not etched in this manner at this time so that they can serve as a proper mask for over-etching (e.g., page 16, line 19 - page 17, line 15). The compensation patterns are removed by further etching (page 17, lines 16-18). Therefore, Figs. 2B, 2C, 3B, 3C, 4B, 4C, 5B, 5C, 6B and 6C have now been corrected to show only the silicon wafer during and after the etching progress.

Wherefore, Applicant respectfully requests entry of the new, corrected drawings.

Applicant's undersigned attorney may be reached in our New York office by telephone at (212) 218-2100. All correspondence should continue to be directed to our address given below.

Respectfully submitted,



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